



INTERNATIONAL MICROELECTRONICS
AND PACKAGING SOCIETY



Nesjavellir Geothermal Power Station

Douglas MacGugan
doug.macgugan@honeywell.com
Redmond, WA USA

DM300 – A 300°C Geothermal Directional Module Development

HiTEC 2012





Acknowledgements

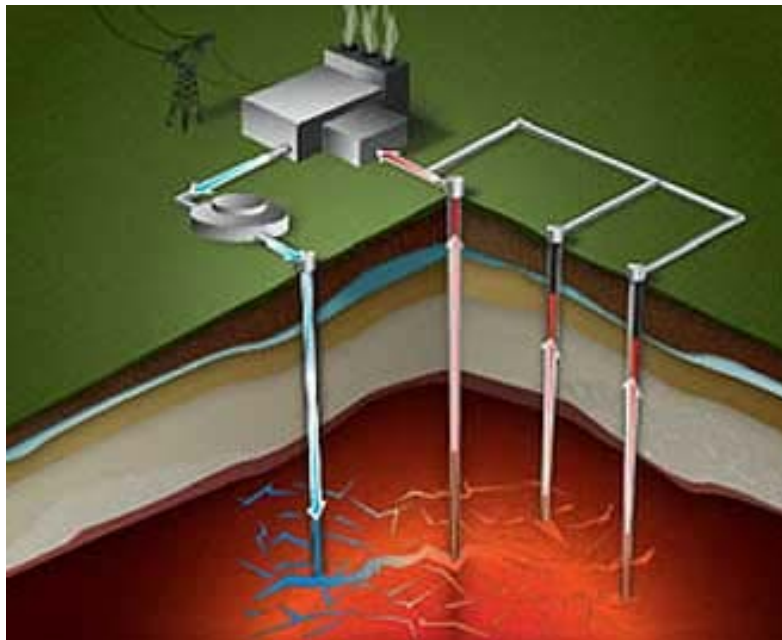
This material is based upon work supported by the U.S. Department of Energy under, Golden Field Office, award number DE-EE0002574.

Development Partners:

Honeywell – Aerospace, Defense & Space – Redmond, WA

Honeywell - Microelectronics & Precision Sensors, Plymouth, MN

Applied Physics Systems, Mountain View, CA



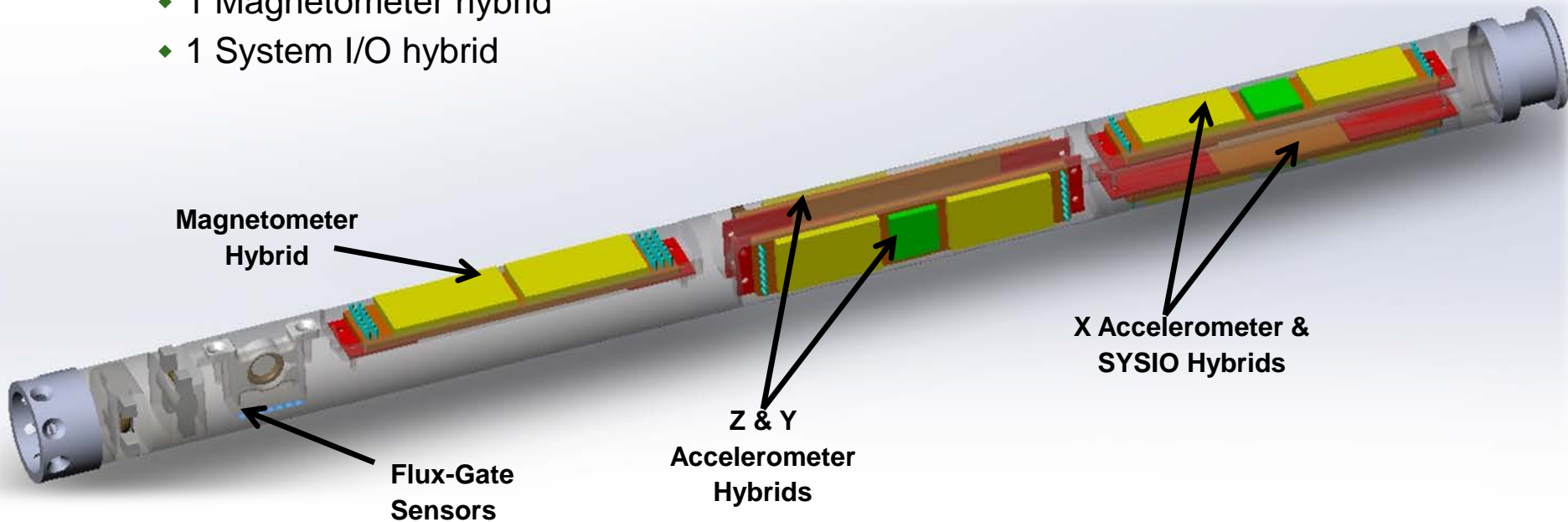
This report was prepared as an account of work sponsored by an agency of the United States Government. Neither the United States Government nor any agency thereof, nor any of their employees, makes any warranty, express or implied, or assumes any legal liability or responsibility for the accuracy, completeness, or usefulness of any information, apparatus, product, or process disclosed, or represents that its use would not infringe privately owned rights. Reference herein to any specific commercial product, process, or service by trade name, trademark, manufacturer, or otherwise does not necessarily constitute or imply its endorsement, recommendation, or favoring by the United States Government or any agency thereof.

- **New paradigm for 300°C directional drilling orientation instrument**
 - **3 orthogonal sensors referencing gravity and magnetic vector**
 - ◆ Flux-gate magnetometers
 - ◆ Vibrating beam accelerometer (VBA)
 - **Minimize electronics complexity**
 - ◆ Utilize frequency based pseudo-digital sensors
 - ◆ Digital outputs from sampling frequency periods/phase over selected gate time
 - **Address materials issues and processes**
 - ◆ Titanium housing and mechanical interconnect
 - ◆ Flux-gate core, bobbin, and windings
 - ◆ Hermetically sealed silicon MEMS VBA
 - ◆ High-temperature Co-fired Ceramic (HTCC) hybrid electronics
 - ◆ Chip & wire circuit design
 - ◆ Circuit assembly using stepped-eutectic 80Au/20Sn brazing
 - ◆ CuNi Wire with specially developed >300°C polymer insulation
 - ◆ Interconnects with brazed pins on HTCC and ceramic SIP header
 - ◆ Connectors with non-polymer pin encapsulants

Directional Module Mechanical Design

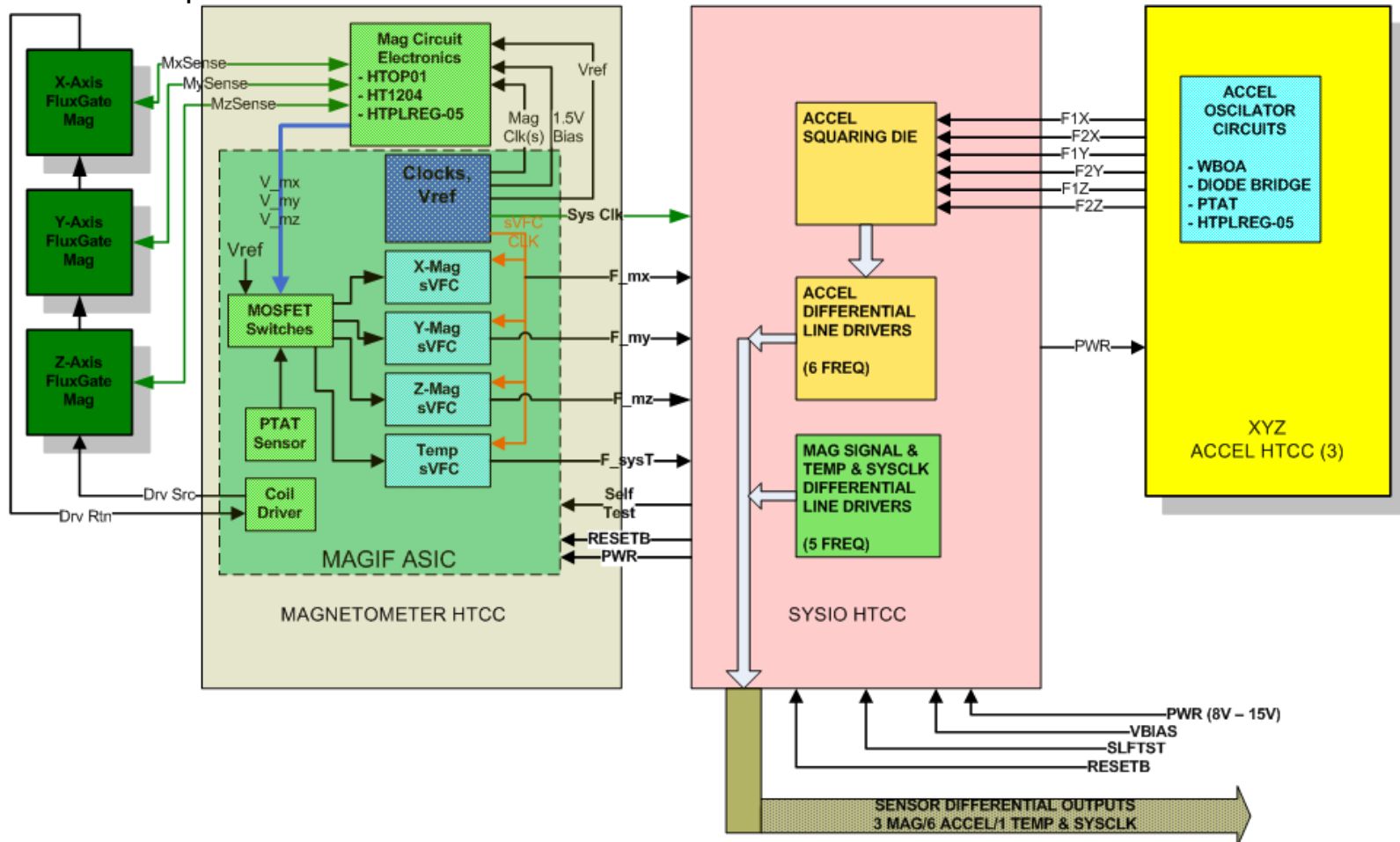
- **DM300 – Features**

- ~1.2” dia titanium housing (1.25” dia with cover tube)
- Titanium end fixtures – laser welded to housing
 - ◆ High end – electrical connector
 - ◆ Lo end – mechanical interface
- **5 HTCC hybrid electronic boards + 3 flux-gate magnetometers**
 - ◆ 3 VBA accelerometer hybrids
 - ◆ 1 Magnetometer hybrid
 - ◆ 1 System I/O hybrid



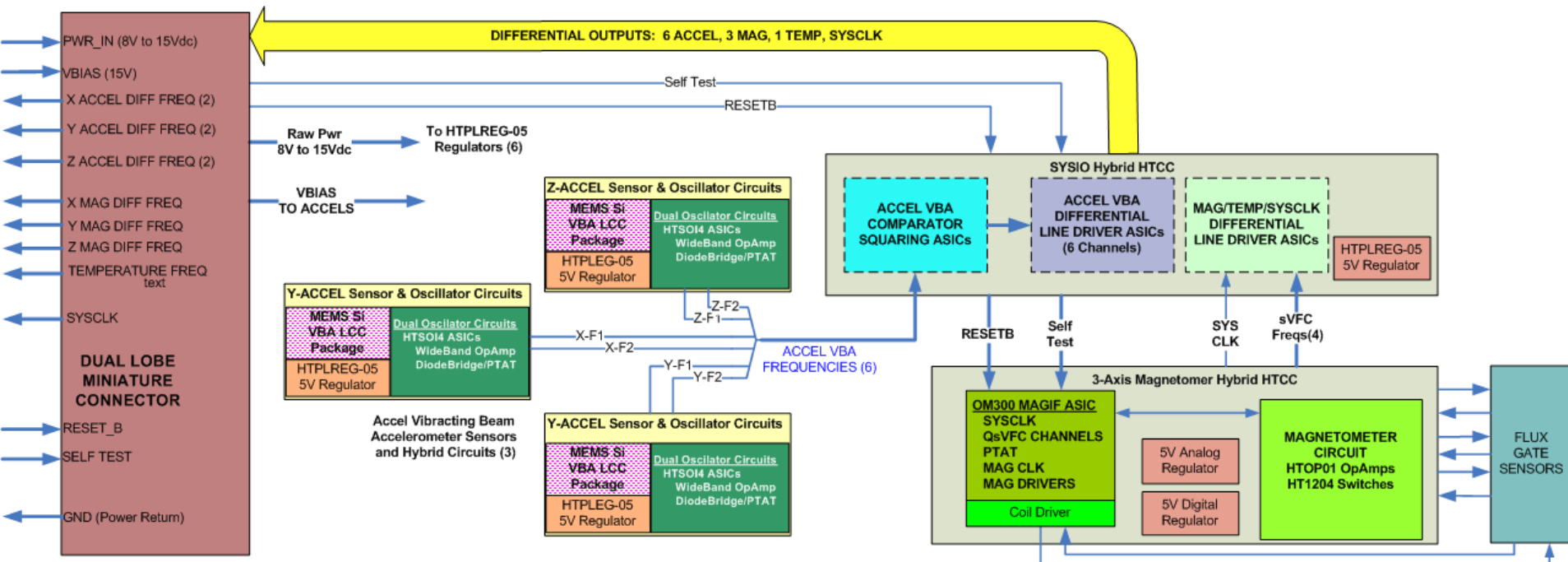
DM300 – Block Diagram

- 300°C Sensor demonstration
 - Frequency outputs with minor handshaking
 - ◆ 3 Magnetometer frequencies
 - ◆ 6 Accelerometer frequencies (2 from each VBA)
 - ◆ Temperature and SYSCLK



DM300 – 300°C Interconnect Approach

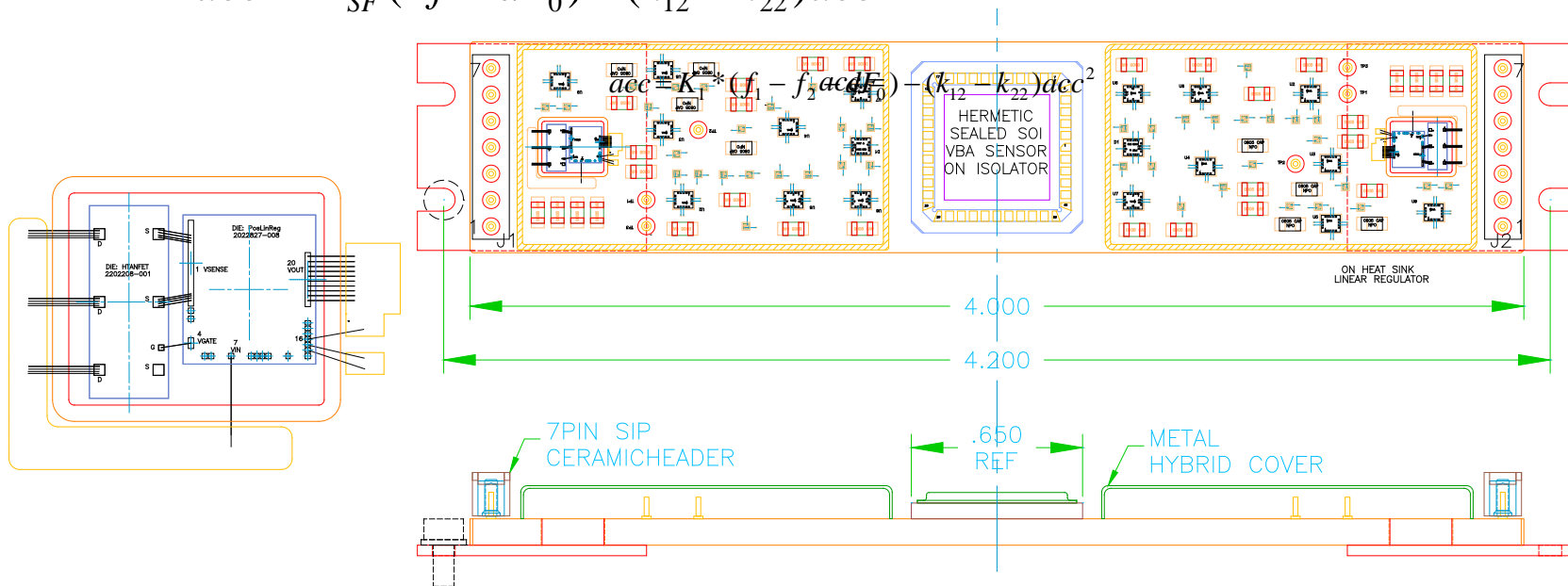
- Hybrids mount directly onto Ti housing using heat-sink plates
- Hybrid-to-hybrid interconnect from brazed pins on hybrid
 - Wires routed in channels machined into housing
- Module connector
 - 15-pin dual lobe sub-miniature
 - Non-polymer pin encapsulant



DM300 – Hybrid Circuits

- Common 4" x .8" size with CuW heat plate mounts
- Independent power-regulator die on heat sink
- Vibrating Beam Accelerometer (VBA)
 - Silicon MEMS Sensor in hermetic sealed LCC
 - Two oscillator circuits – Using HTSOI4 custom components
 - Frequency output proportional to sensed acceleration

$$acc = K_{SF} (\Delta f - dF_0) - (k_{12} - k_{22}) acc^2$$

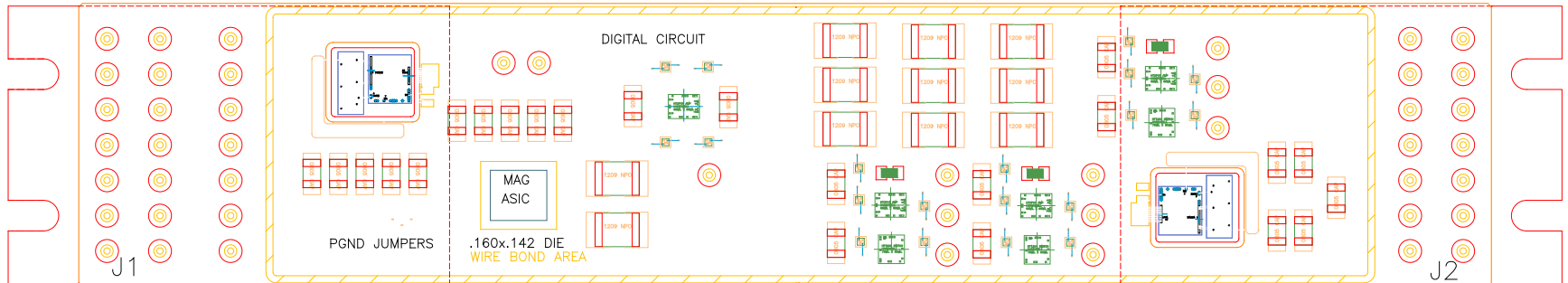
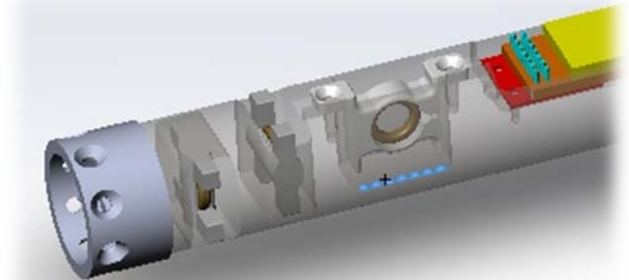


MEMS – Micro-machined Electro-Mechanical Systems

DM300 – Hybrid Circuits

- **Magnetometer**

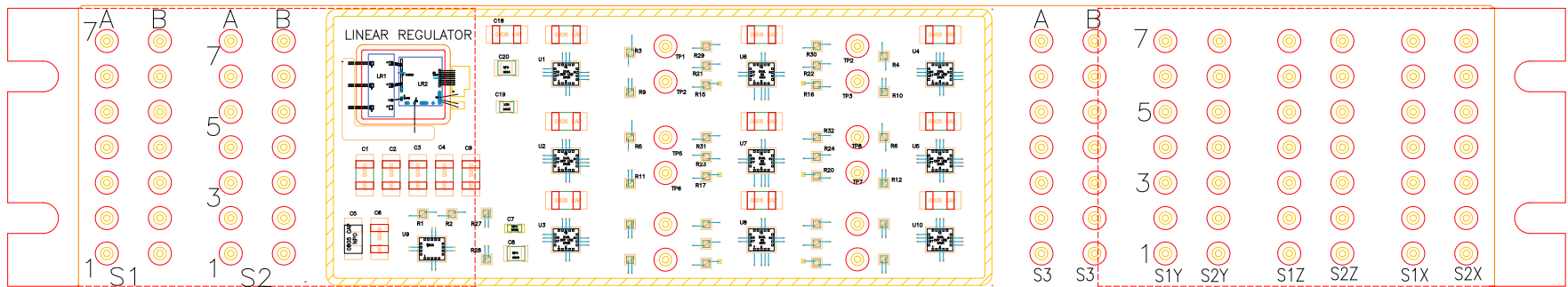
- **Three flux-gate sensors**
- **2nd Harmonic drive & sense circuit**
- **Honeywell 300°C HTSOI4 Components**
 - ◆ MAGIF ASIC with clocks, Quad-sVFC, and coil drive functions
 - ◆ Dual op-amp and quad switches



sVFC – Synchronous Voltage-to-Frequency Converter

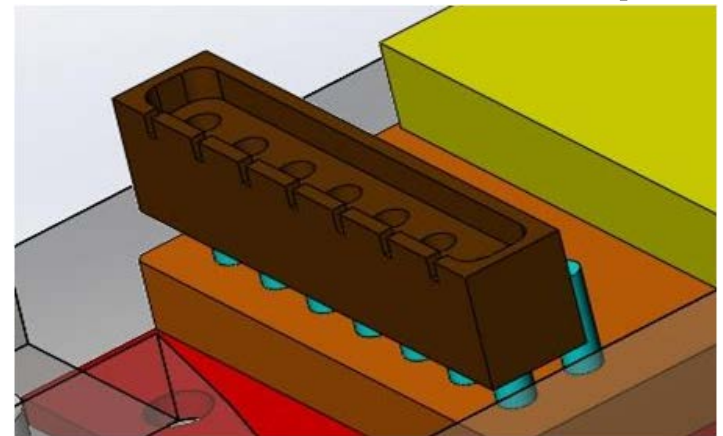
- **SYSIO HTCC**

- Gathers sensor signals and outputs via twisted pair to test system
- Squares VBA frequency signals – 300°C HTSOI4 comparator
- Outputs frequency signals to test system – HTSOI4 differential driver

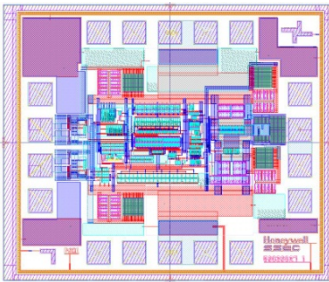


- **Interconnects using custom 7-pin SIP header on brazed HTCC pins**

- Ceramic body
- BeNi contact inserts
- TIG welded 300°C CuNi wire



- **Complete set of 300°C SOI chips designed and fabricated**
 - All tested and validated at 300°C
 - Common footprint and pad arrangement

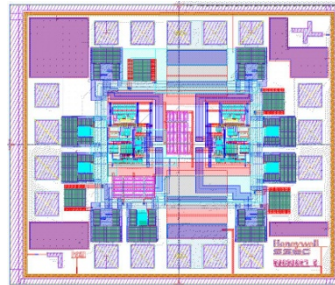


Wide-band Opamp

Multiple instances used on each for Accelerometer CCA for interface and signal conditioning

15.8MHz Unity gain bandwidth, 45° phase margin at 300C (15pF load)

3 Versions with varying levels of ESD protection



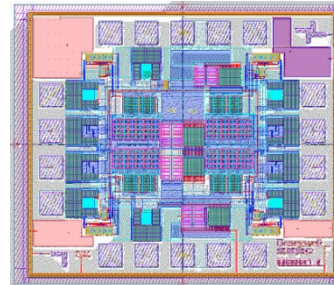
Dual Comparator

Squares VBA frequency outputs to full CMOS logic levels

Built in hysteresis (Enabled/Disable)

Fast response for minimal skew/jitter of freq outputs.

Propagation delay at 300C ≤ 40 nsec
100mV pk-pk input (into 12pF load)

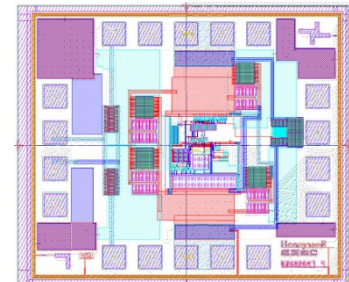


Quad Line Driver

Configurable as Quad single ended or Dual Differential output.

Differential-mode output is 3V (minimum) into 120 Ω termination

Outputs can be tri-stated by control input



Temperature Sensor & Small-signal diode bridge

(PTAT) current source : temperature sensor for system calibration.

Diode bridge VBA drive limiter

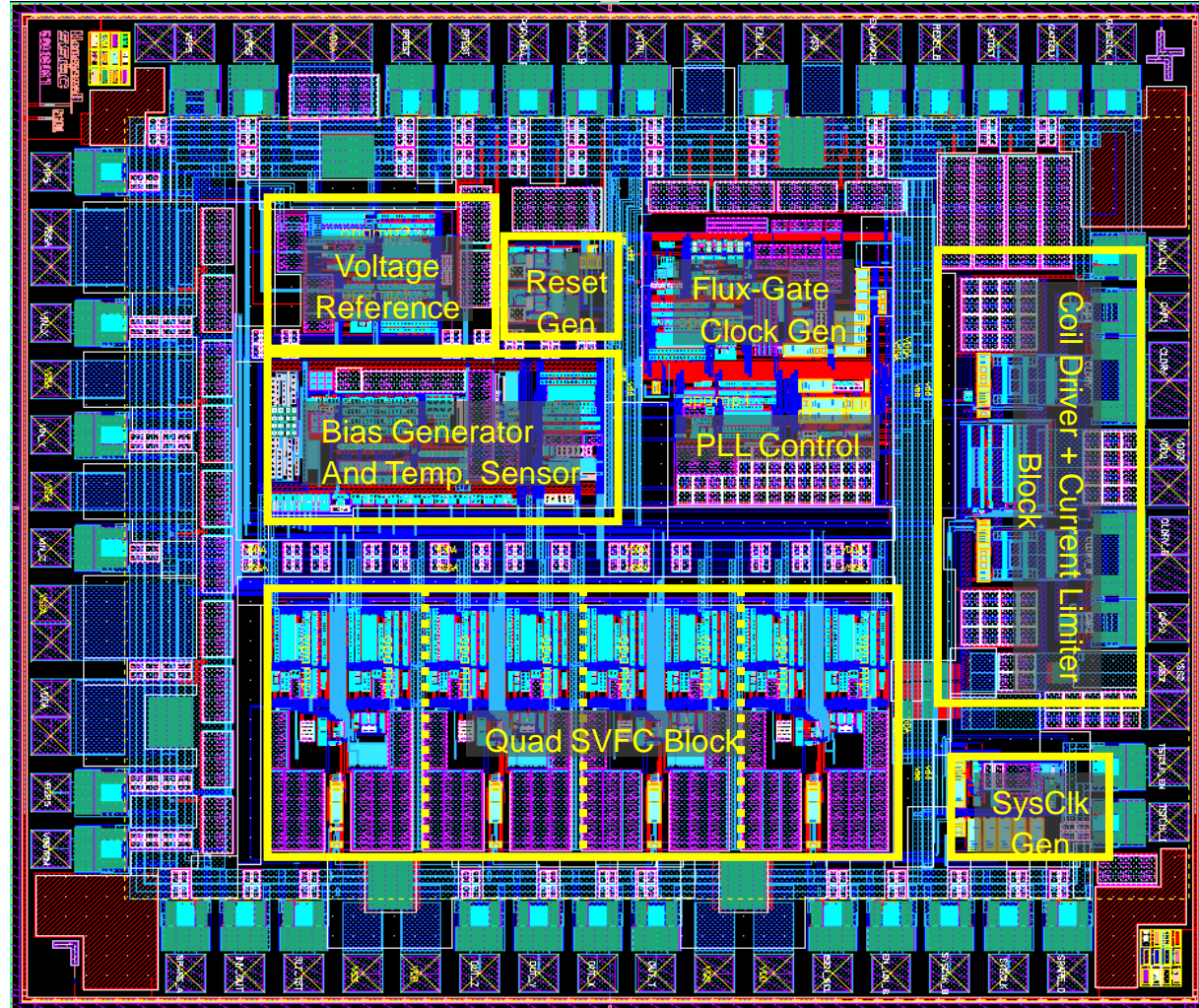
Magnetometer Interface ASIC

Die Size ~ 160 x 141 mils

61 Bond Pads Total

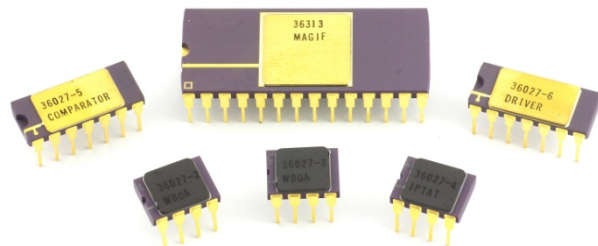
Major Function Blocks

- Quad synchronous Voltage-to-Frequency Converter (sVFC)
- Bias Generator and Temp. Sensor
- Voltage Reference Block
- Flux-gate Clock Generator w/Phase-Locked Loop Control
- Coil Driver + Current Limiter Block
- System Clock Generator
- Reset Generator

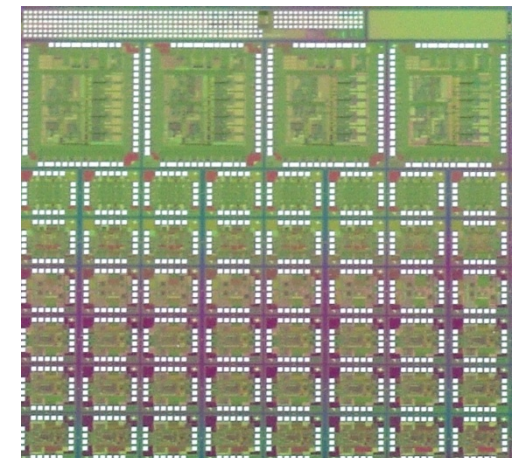


DM300 300°C SOI Fabrication & Usage

- Custom DM300 Die on Single Reticle
 - Yield \geq several hundred: 3-wafer lot
 - Common footprint + MagIF ASIC
- Catalog HTSOI4 components have been sample tested at 300°C
 - HTPLREG-05: 5V Linear Voltage Regulator
 - HT1204: Quad Analog Switch
 - HTOP01: Dual Precision Operational Amplifier



14.6 mm							
Wafer Process Monitor Testing Structures							
MagIF ASIC		MagIF ASIC		MagIF ASIC		MagIF ASIC	
Quad Digital Buffer	Quad Digital Buffer	Quad Digital Buffer	Quad Digital Buffer	Quad Digital Buffer	Quad Digital Buffer	Quad Digital Buffer	Quad Digital Buffer
Dual Comparator	Dual Comparator	Dual Comparator	Dual Comparator	Dual Comparator	Dual Comparator	Dual Comparator	Dual Comparator
Diode-bridge and PTAT Current Source	Diode-bridge and PTAT Current Source	Diode-bridge and PTAT Current Source	Diode-bridge and PTAT Current Source	Diode-bridge and PTAT Current Source	Diode-bridge and PTAT Current Source	Diode-bridge and PTAT Current Source	Diode-bridge and PTAT Current Source
Wide-Band OpAmp: Standard ESD	Wide-Band OpAmp: Standard ESD	Wide-Band OpAmp: Standard ESD	Wide-Band OpAmp: Standard ESD	Wide-Band OpAmp: Standard ESD	Wide-Band OpAmp: Standard ESD	Wide-Band OpAmp: Standard ESD	Wide-Band OpAmp: Standard ESD
Wide-Band OpAmp: 0.1X ESD	Wide-Band OpAmp: 0.1X ESD	Wide-Band OpAmp: 0.1X ESD	Wide-Band OpAmp: 0.1X ESD	Wide-Band OpAmp: 0.1X ESD	Wide-Band OpAmp: 0.1X ESD	Wide-Band OpAmp: 0.1X ESD	Wide-Band OpAmp: 0.1X ESD
Wide-Band OpAmp: 0.01X ESD	Wide-Band OpAmp: 0.01X ESD	Wide-Band OpAmp: 0.01X ESD	Wide-Band OpAmp: 0.01X ESD	Wide-Band OpAmp: 0.01X ESD	Wide-Band OpAmp: 0.01X ESD	Wide-Band OpAmp: 0.01X ESD	Wide-Band OpAmp: 0.01X ESD
14.4 mm							



DM300 – Full System Function (Future Development)

- **Replace SYSIO board with “SMART” system**
 - Incorporate development from “Deep Trek” program
 - ◆ Reconfigurable Programmable Data Acquisition (RPDA)
 - ◆ Replace FPGA from RPDA with Honeywell HT2300 Gate Array
 - ◆ Eliminate SRAM requirement
 - ◆ Utilize 32kbyte EEPROM
 - Has demonstrated >100,000 read-write cycles up to 300°C
 - Store system ID and sensor characterization data
 - **Utilize RPDA MCM ceramic HTCC**
 - ◆ Incorporate onto new DM300 system level HTCC (same 4” x .8” size)
- **Gate Array captures and formats data**
 - Counters for frequency signals
 - EEPROM control
 - SPI Bus communications
- **Possibility of including other down-hole functionality into gate array**

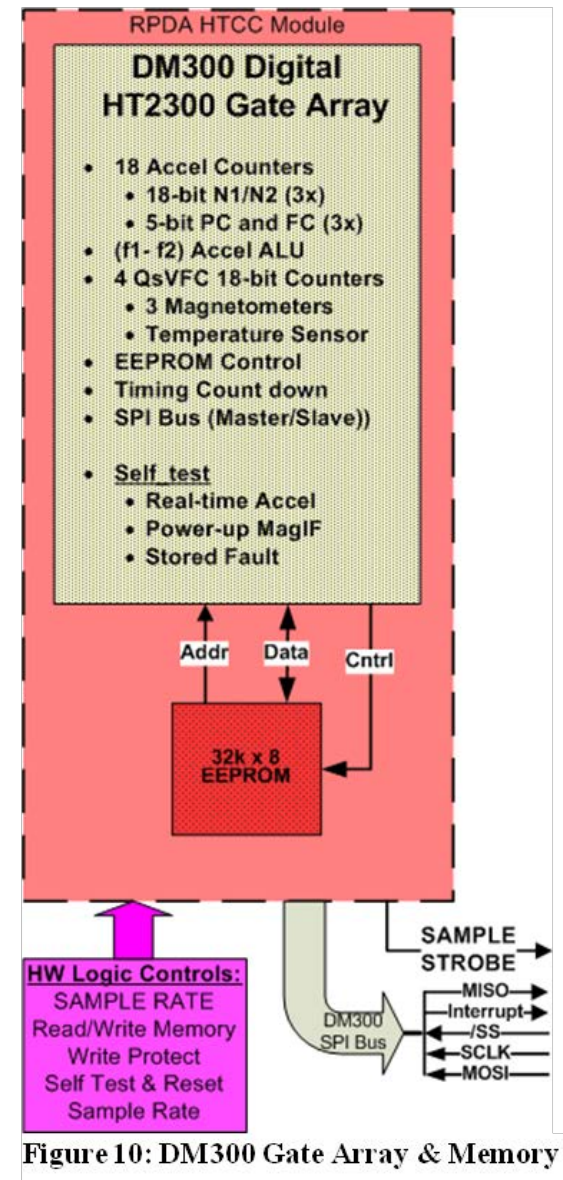


Figure 10: DM300 Gate Array & Memory

DM300 – 300°C Directional Module Summary

- **Demonstration of base module and sensor characterization**
 - Frequency based sensor system – eliminates need for ADC
 - **Electronic circuits developed and hybrids in fabrication**
 - ◆ Utilize step-AuSn braze for component mount
 - ◆ Independent power regulation on each hybrid
 - ◆ All chip & wire construction
 - **Active electronics fabricated and validate at 300°C**
- **Mechanical issues resolved**
 - Titanium housing, connector, and mechanical interface
 - Ceramic hybrid mounting with heat sinking
 - 300°C wiring and board-to-board interconnect routing
- **Sensor development finalized**
 - Silicon MEMS VBA
 - Flux-gate magnetometers with sVFC electronics
- **Operational demonstration scheduled for October**

New paradigm for 300°C directional drilling module nearing completion